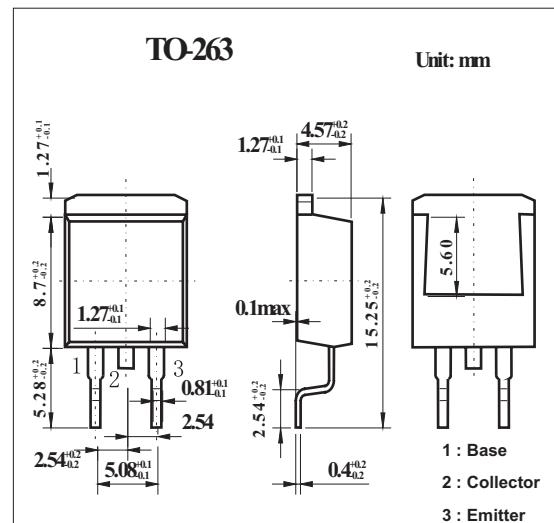


Switching Applications

2SD2198

■ Features

- Surface mount type device making the following possible.
- Low collector-to-emitter saturation voltage.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	60	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	6	V
Collector current	I _C	5	A
Collector current (pulse)	I _{CP}	9	A
Collector dissipation	P _C	1.65	W
T _C = 25°C		30	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

2SD2198■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 40\text{V}$, $I_E = 0$			0.1	mA
Emitter cutoff current	I_{EBO}	$V_{EB} = 4\text{V}$, $I_C = 0$			0.1	mA
DC current Gain	h_{FE}	$V_{CE} = 2\text{V}$, $I_C = 1\text{A}$	70		280	
		$V_{CE} = 2\text{V}$, $I_C = 3\text{A}$	30			
Gain bandwidth product	f_T	$V_{CE} = 5\text{V}$, $I_C = 1\text{A}$		30		MHz
Output capacitance	C_{ob}	$V_{CB} = 10\text{V}$, $f = 1\text{MHz}$		100		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 3\text{A}$, $I_B = 0.3\text{A}$			0.4	V
Collector-to-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 1\text{mA}$, $I_E = 0$	60			V
Collector-to-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}$, $R_{BE} = \infty$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 1\text{mA}$, $I_C = 0$	6			V
Turn-on time	t_{on}	 10 $I_B1 = 10 I_B2 = I_C = 2\text{A}$ For PNP, the polarity is reversed. Unit (resistance : Ω , capacitance : F)		0.1		μs
Storage time	t_{stg}			1.4		μs
Fall time	t_f			0.2		μs

■ h_{FE} Classification

Rank	Q	R	S
h_{FE}	70~140	100~200	140~280